LISTING of CLAIMS

1-12. (Cancelled)

13. (Currently amended) A process for selectively removing silicon dioxide and photoresist sidewall residue after drywall etching of a semiconductor wafer comprising treating the wafer after dry etching with a solution ~~comprising~~ consisting essentially of;

(a) sulfuric acid,

(b) ~~a fluorine containing compound~~ hydrofluoric acid, ammonium fluoride or an alkali metal fluoride,

and

(c) hydrogen peroxide,

wherein said solution contacts said sidewall residue effectively to remove it from said dry etched wafer,

and wherein the ratio (a):(b) is in the range of from 10:1 to 700:1 by weight.

14. (Currently amended) A process for removing photoresist according to claim 13, wherein the photoresist is effective for g-line, i-line, deep UV, E-beam or X-ray.

15. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated at a temperature of from 0 to 140 degrees C.

16. (Currently amended) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated for about 10 minutes.

17. (Currently amended) A process for removing photoresist after dry etching according to claim 13, wherein the operation pressure is maintained at about 1 atm.

18. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the etch rate of the wafer is less than 1 Å/min.

19. (Currently amended) A process for removing photoresist after dry etching according to claim 15, wherein the wafer is treated at a temperature of from 120 to 140 degrees C.

20. (Previously presented) A process for removing photoresist after drywall etching according to claim 13, wherein the fluorine containing compound is hydrofluoric acid.

21. (Previously presented) A process for removing photoresist after drywall etching according to claim 20, wherein the ratio of sulfuric acid to hydrofluoric acid and hydrogen peroxide is 3:1 by volume.

22. (Cancel)

23. (Cancel)